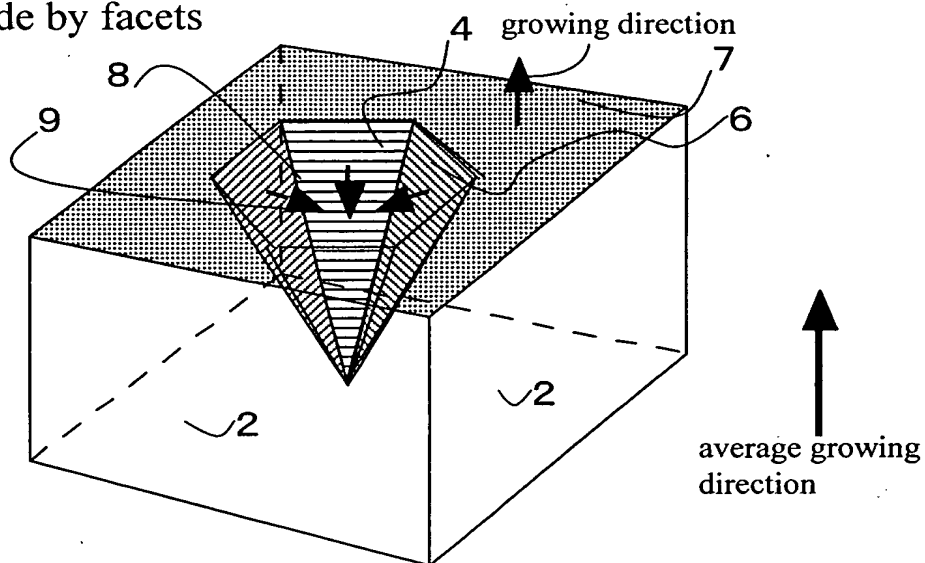


Fig.1

Prior Art

decrement of dislocations by a pit made by facets

(a) a pit made by facets



(b) after continual growth

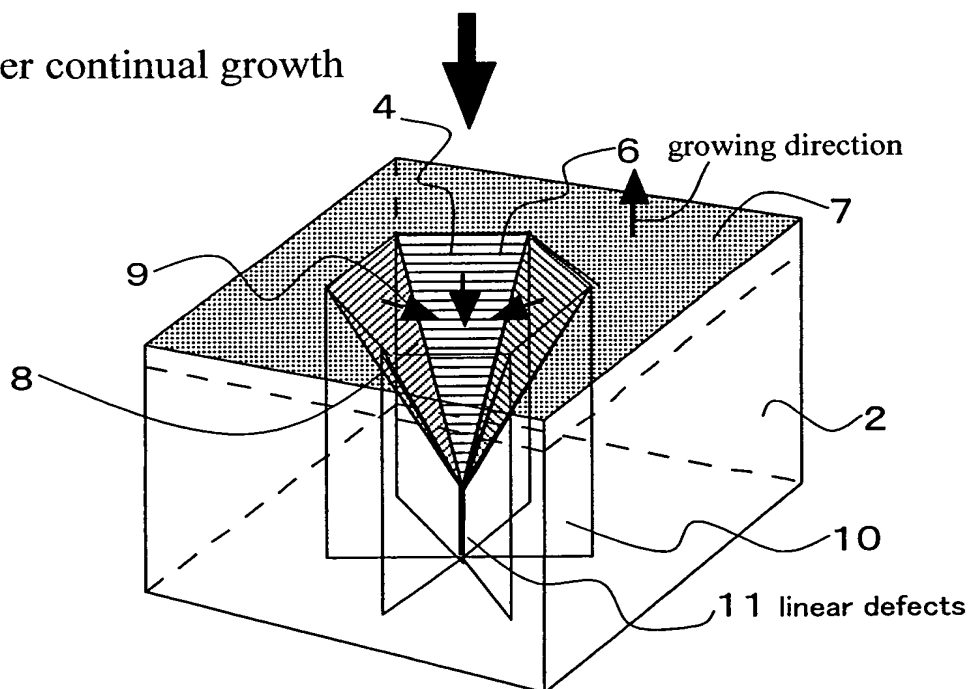


Fig.2

Prior Art

Movements of dislocations inside a pit made by facets

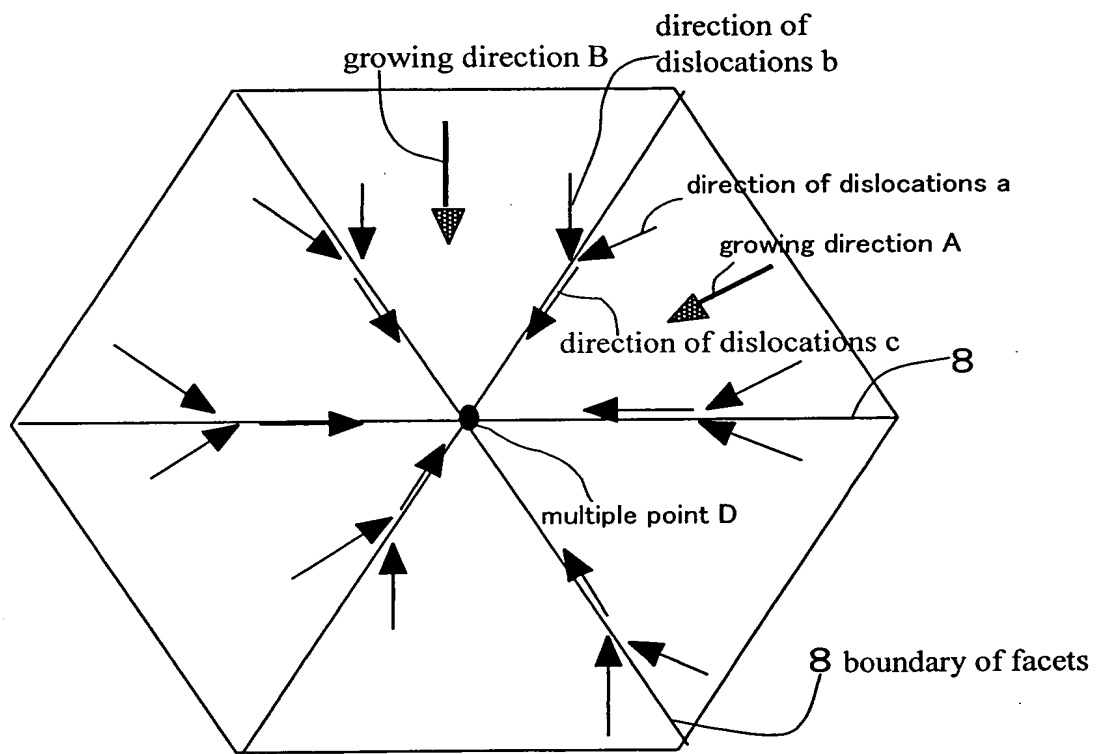


Fig.3

Prior Art
facet growth

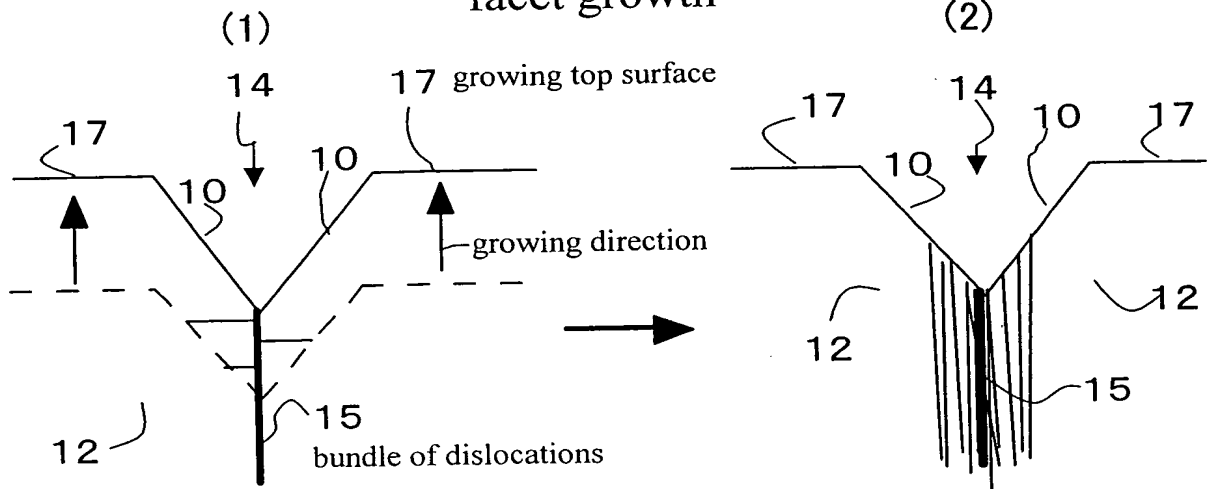


Fig.4 growing method of the present invention

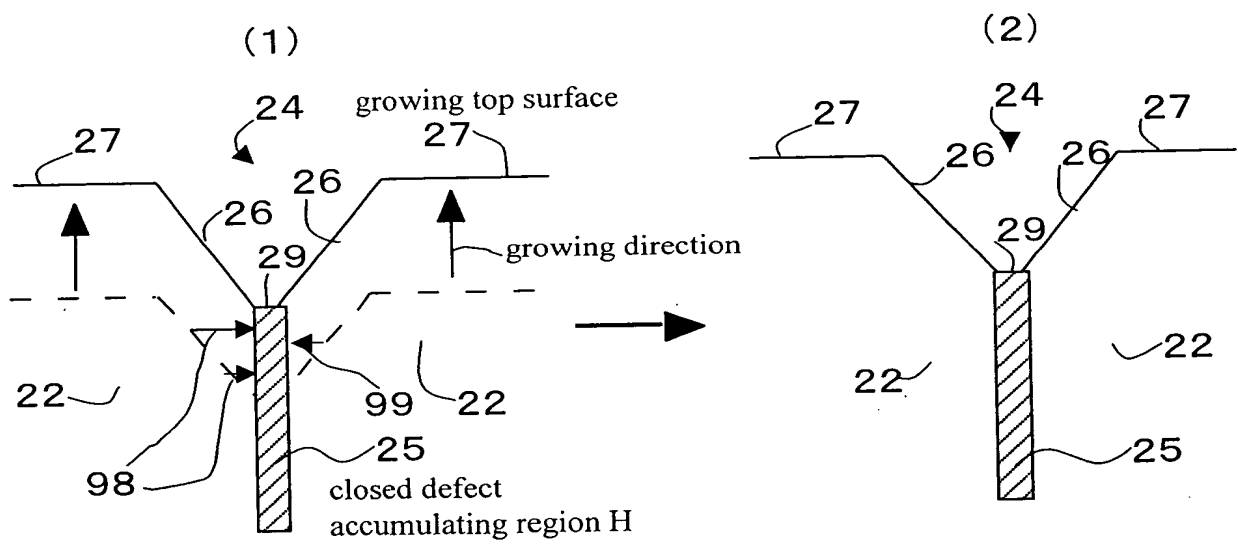


Fig.5 relation between seed and closed defect accumulating region H in the present invention

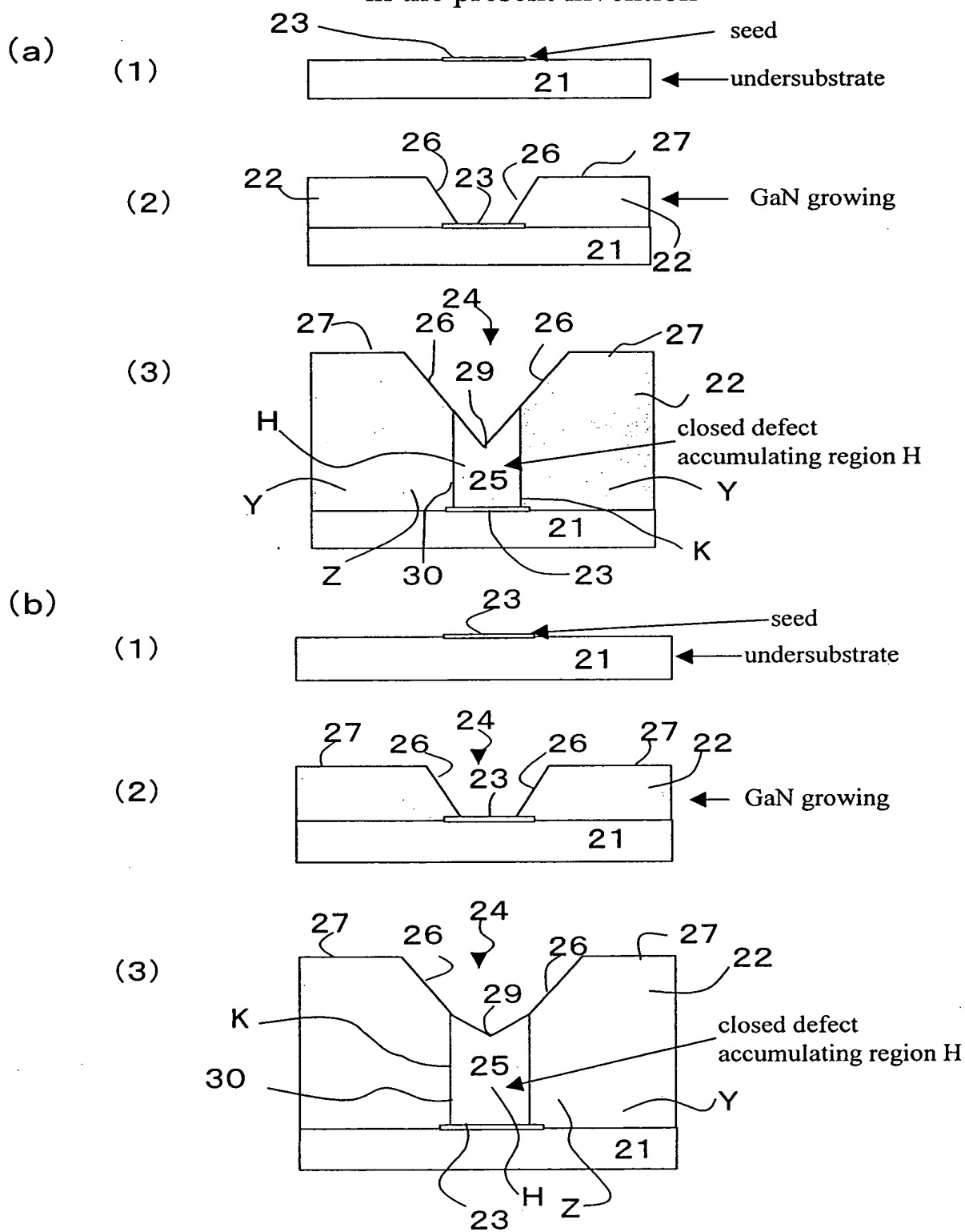


Fig.6

relation between seeds and closed defect accumulating regions H
in the present invention
seed arrangement

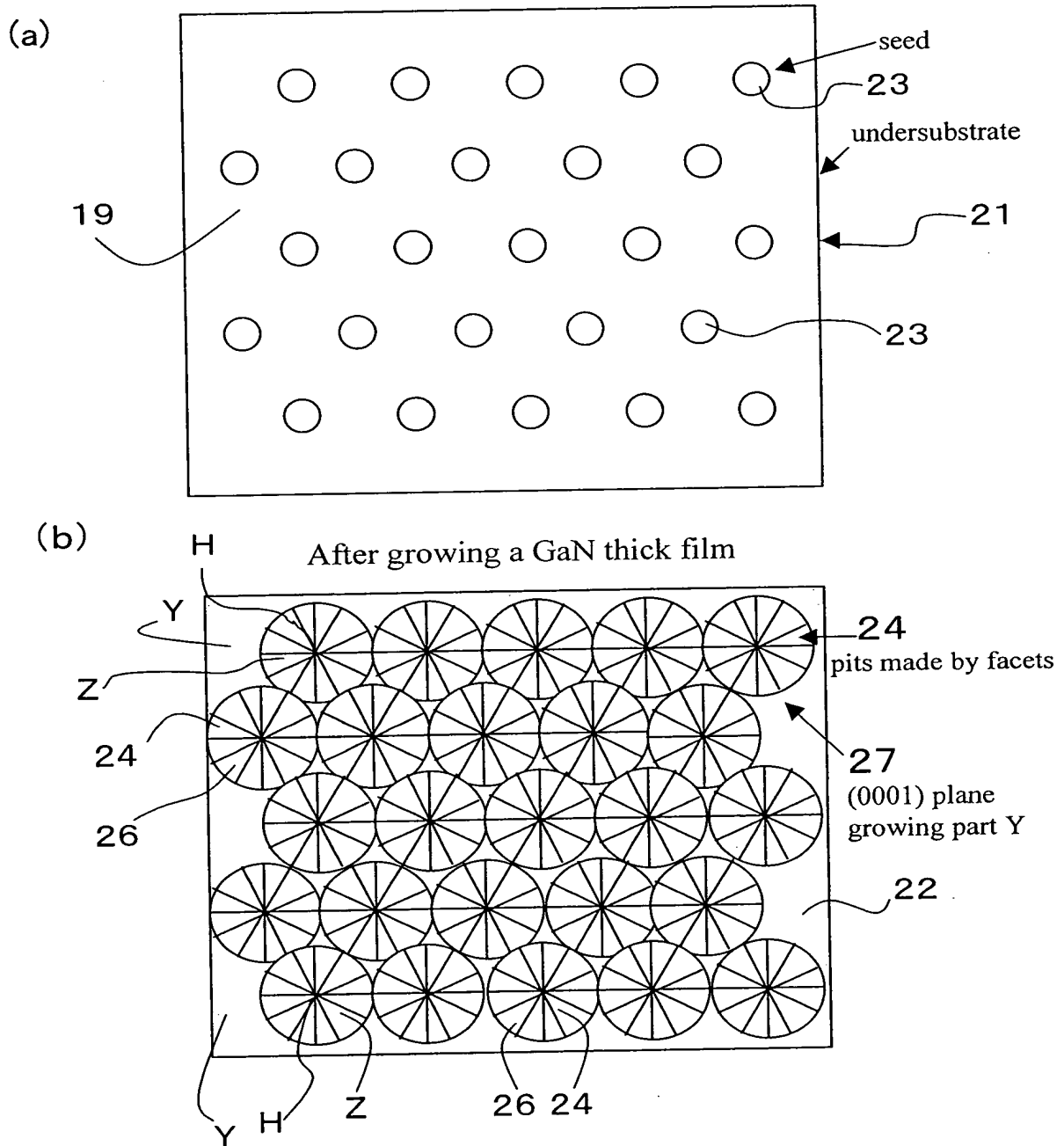


Fig.7

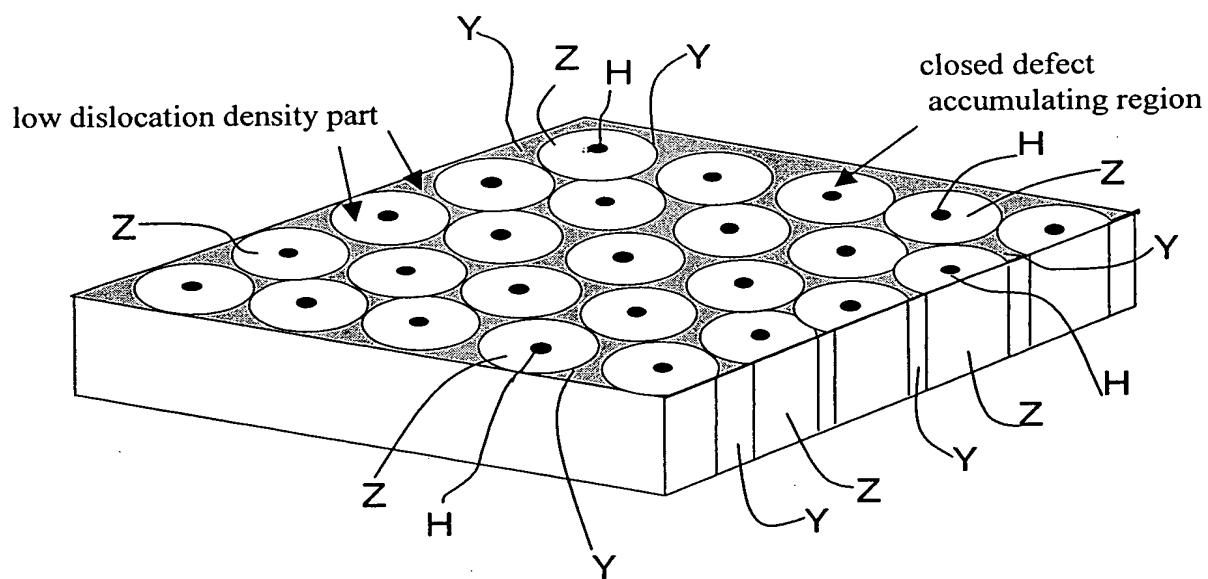


Fig.8

six-fold rotational symmetry arrangement on undersubstrate

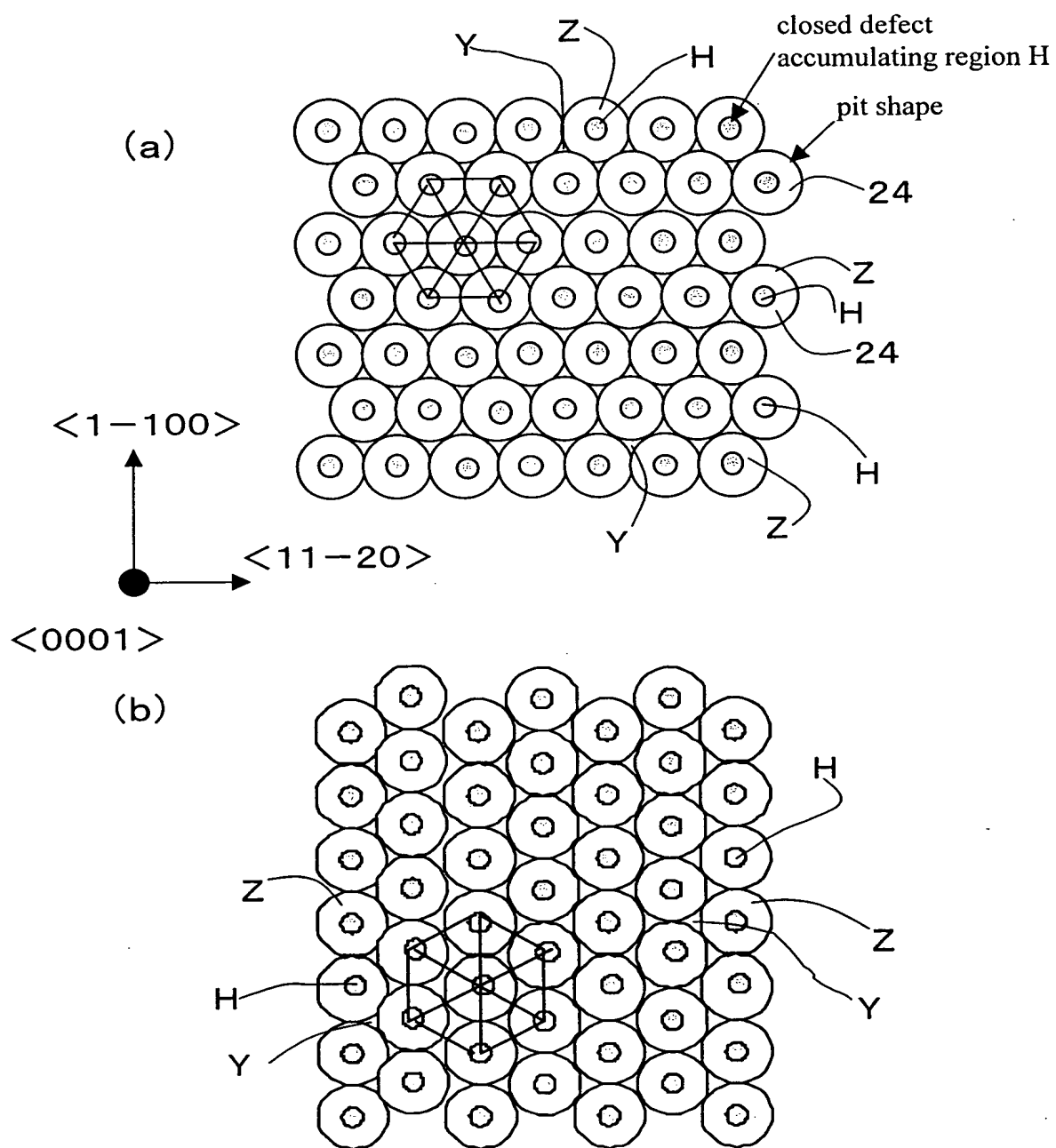


Fig.9 four-fold rotational arrangement on undersubstrate

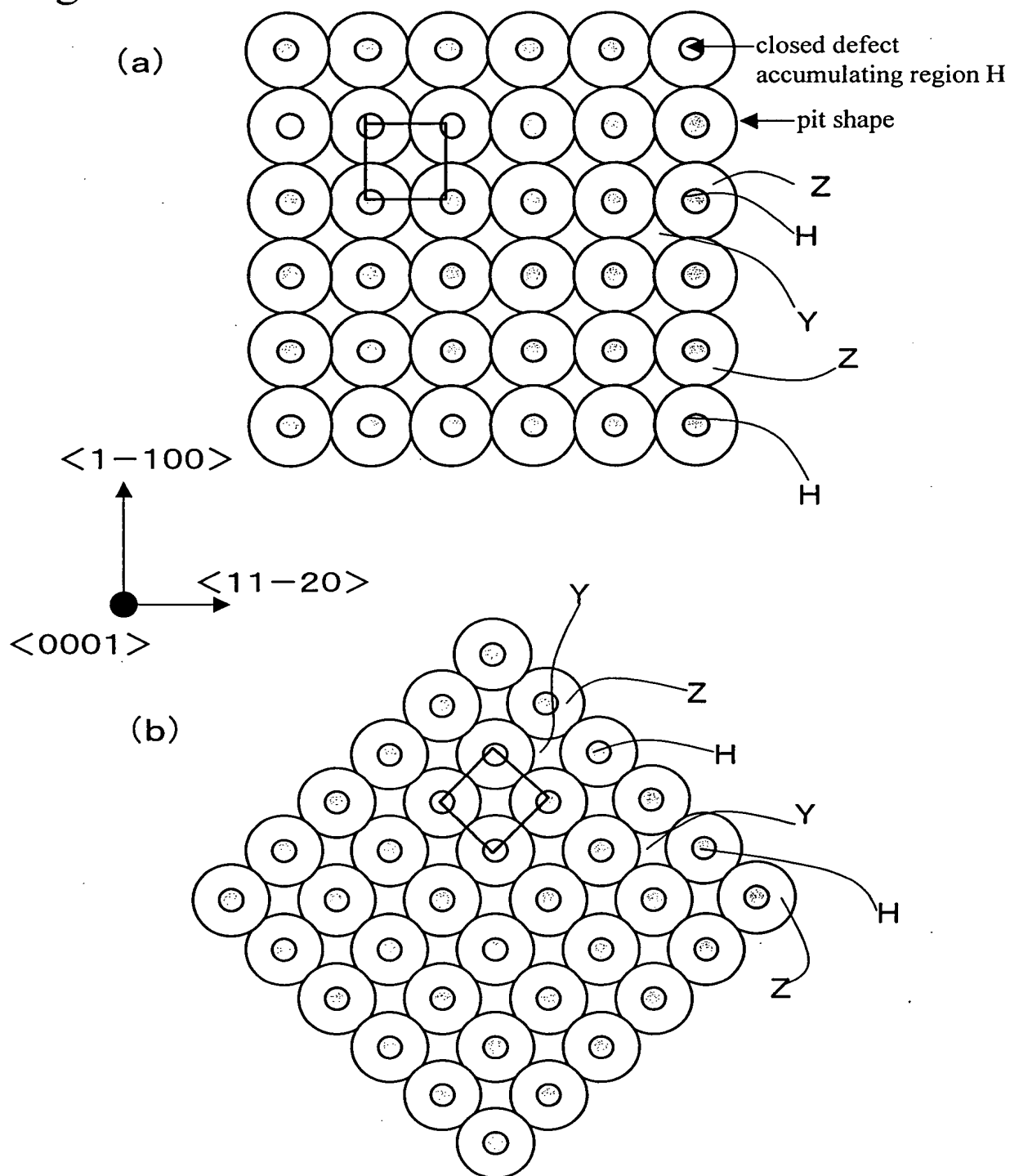


Fig.10

two-fold rotational symmetry arrangement on undersubstrate

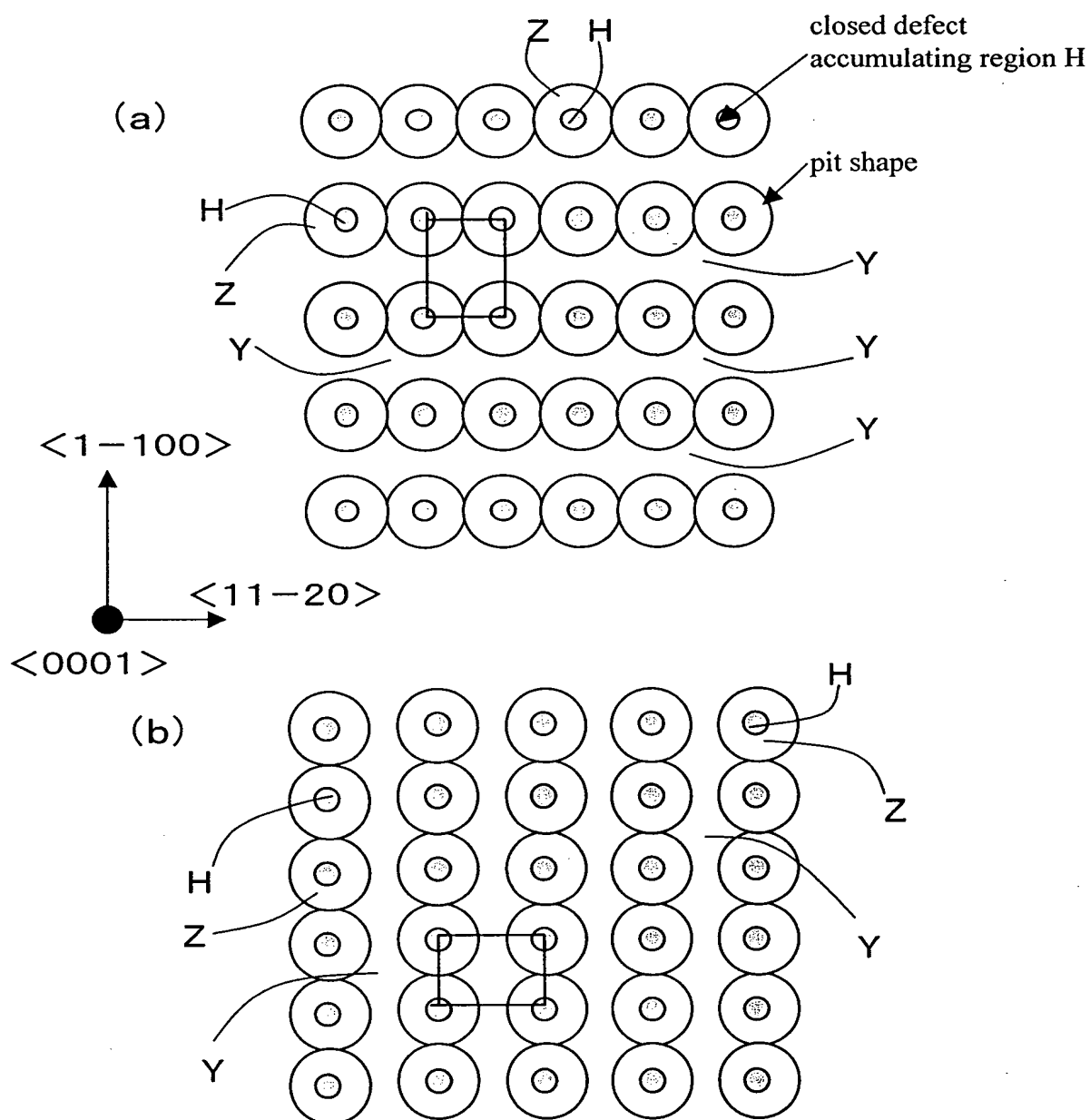


Fig.11

Embodiment 1
Processes of producing a GaN substrate

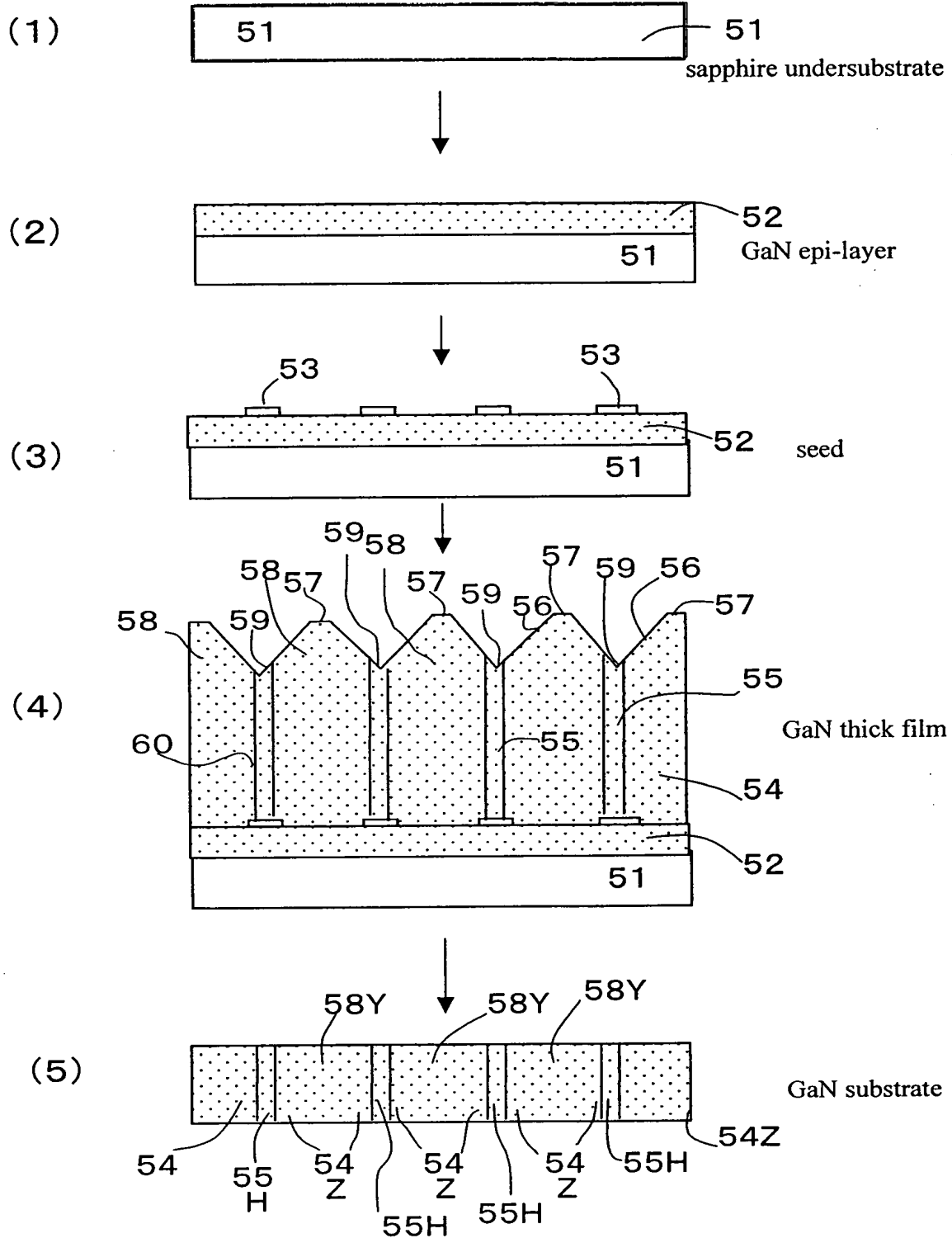


Fig.12

Embodiment 2
processes of producing a GaN substrate

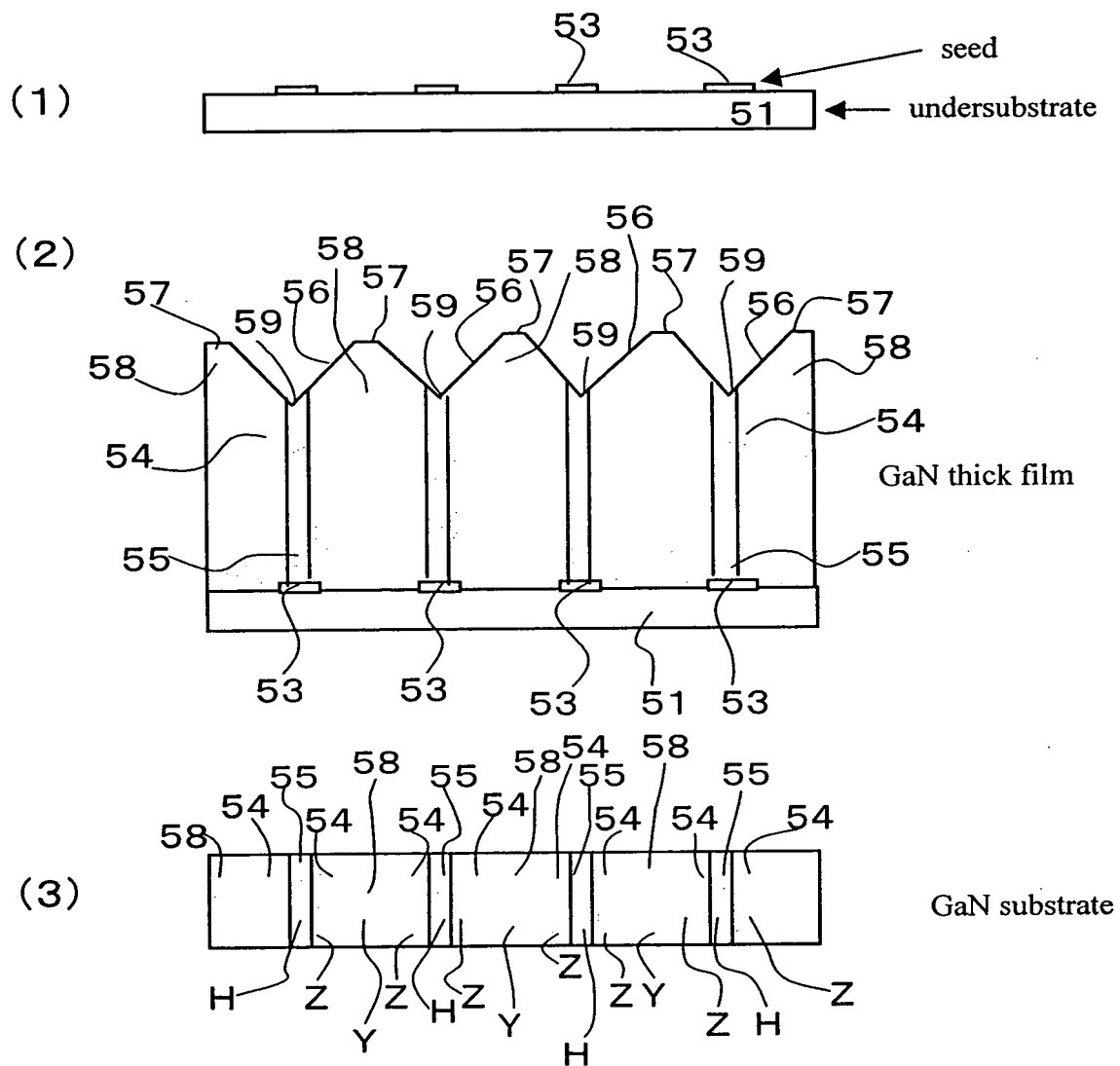
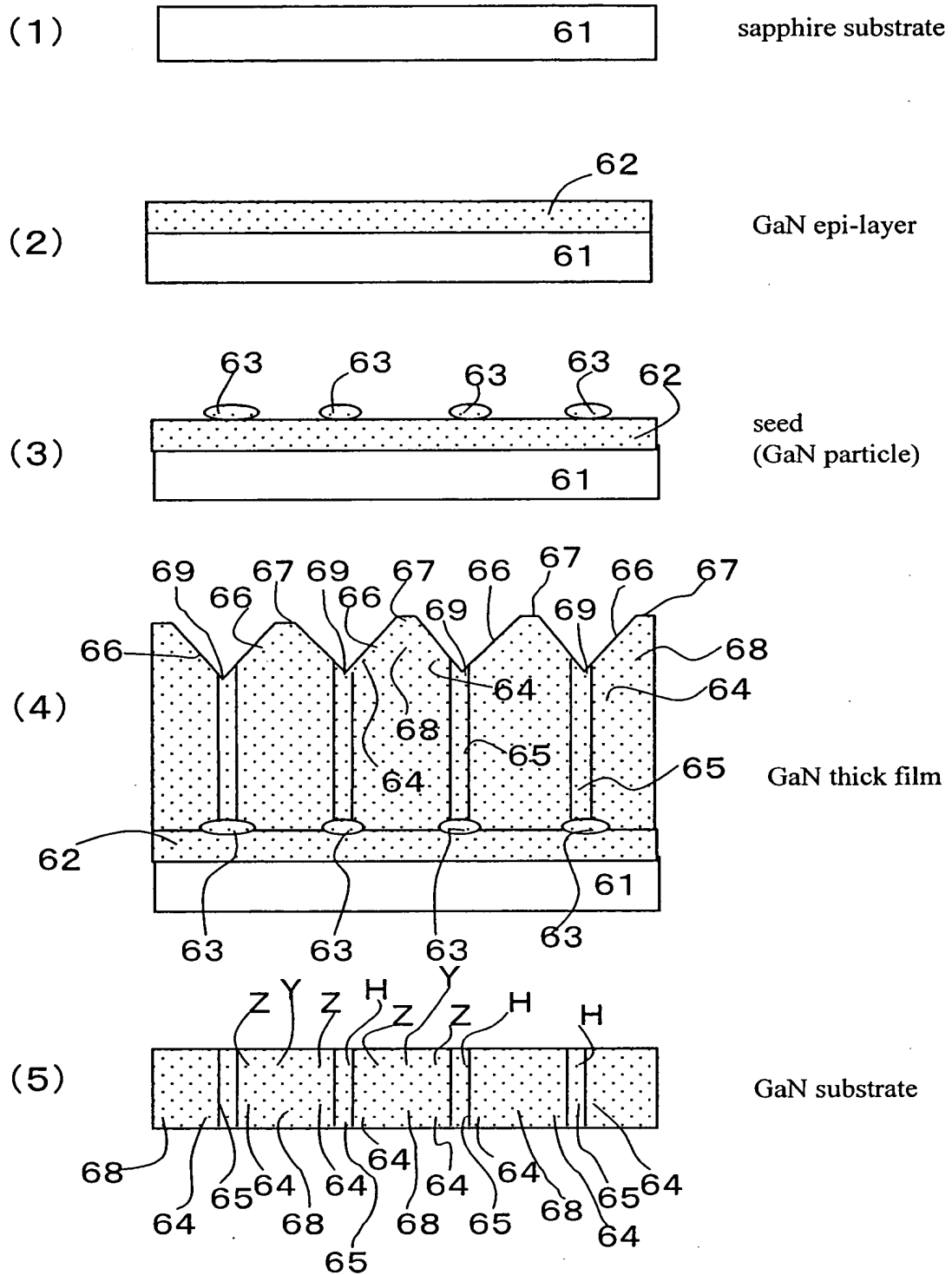


Fig.13 Embodiment 4
Processes of producing a GaN substrate



Embodiment 5

Fig.14 Processes of producing a GaN substrate

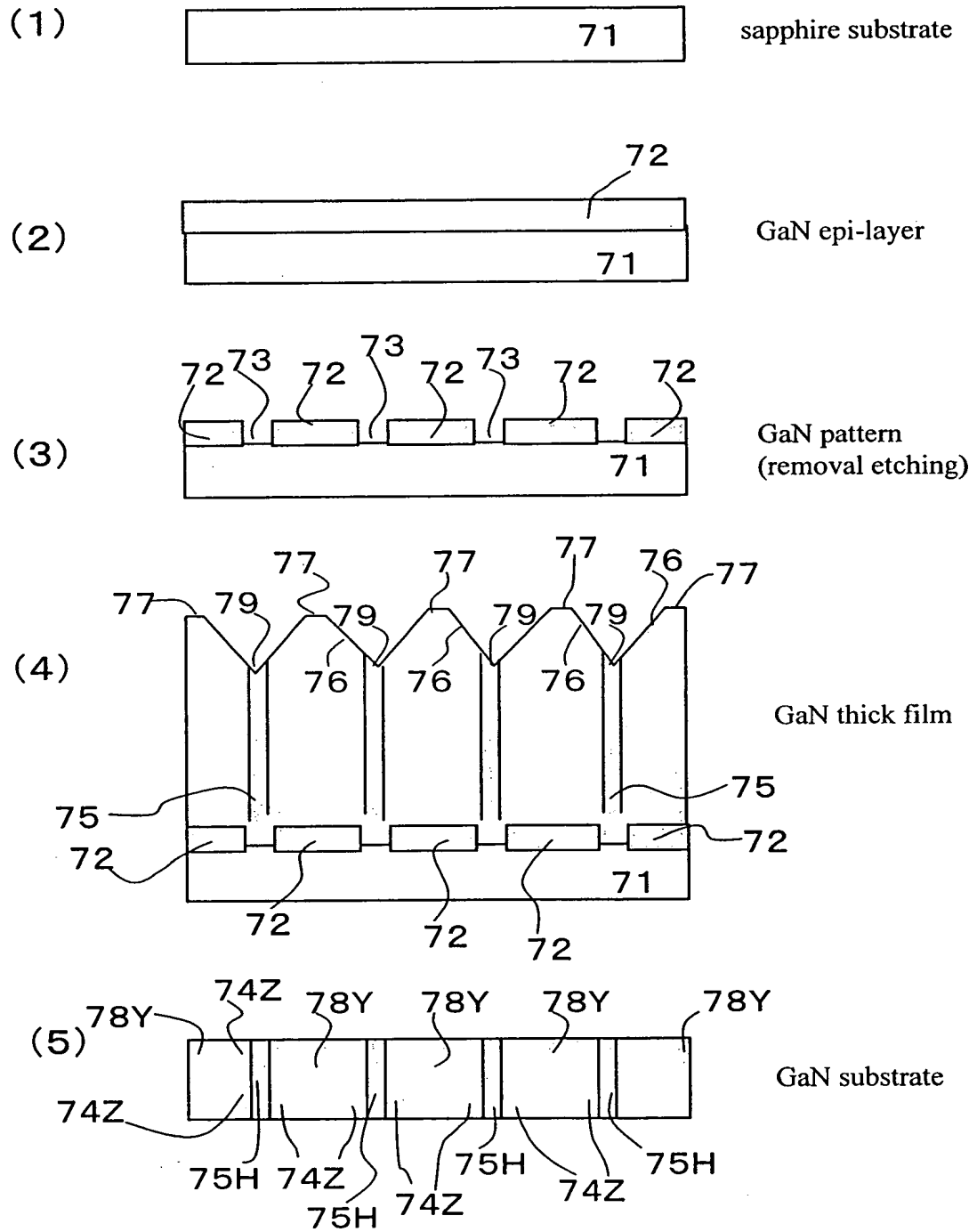


Fig.15

